



ALPHA & OMEGA
SEMICONDUCTOR

AOB411L

60V P-Channel MOSFET

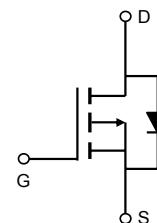
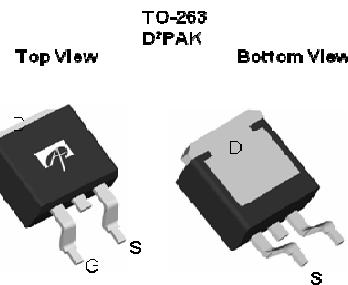
General Description

The AOB411L combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Product Summary

V_{DS}	-60V
I_D (at $V_{GS}=-10V$)	-78A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 16.5mΩ
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 22mΩ

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{T_C=25°C}	I_D	-78	A
Continuous Drain Current ^{T_C=100°C}		-55	
Pulsed Drain Current ^C	I_{DM}	-230	
Continuous Drain Current ^{T_A=25°C}	I_{DSM}	-8	A
Continuous Drain Current ^{T_A=70°C}		-6.5	
Avalanche Current ^C	I_{AS}, I_{AR}	-77	A
Avalanche energy L=0.1mH ^C	E_{AS}, E_{AR}	296	mJ
Power Dissipation ^B	P_D	187	W
		93	
Power Dissipation ^A	P_{DSM}	2.1	W
		1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	11	15	°C/W
Maximum Junction-to-Ambient ^{AD} Steady-State		47	60	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.6	0.8	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-60\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.5	-2	-2.5	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	-230			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-20\text{A}$ $T_J=125^\circ\text{C}$		13.5	16.5	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-20\text{A}$		20.5	25	$\text{m}\Omega$
				17	22	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-20\text{A}$		48		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.7	-1	V
I_s	Maximum Body-Diode Continuous Current ^G				-105	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-30\text{V}, f=1\text{MHz}$	4260	5330	6400	pF
C_{oss}	Output Capacitance		335	483	630	pF
C_{rss}	Reverse Transfer Capacitance		140	234	330	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	1.4	2.8	4.2	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-30\text{V}, I_D=-20\text{A}$	65	83	100	nC
$Q_g(4.5\text{V})$	Total Gate Charge		35	40	50	nC
Q_{gs}	Gate Source Charge			15		nC
Q_{gd}	Gate Drain Charge			18		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-30\text{V}, R_L=1.5\Omega, R_{\text{GEN}}=3\Omega$		17.5		ns
t_r	Turn-On Rise Time			20		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			83.5		ns
t_f	Turn-Off Fall Time			37		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	18	27	36	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	110	165	215	nC

A. The value of R_{vJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on R_{vJA} and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{vJA} is the sum of the thermal impedance from junction to case R_{vJC} and case to ambient.

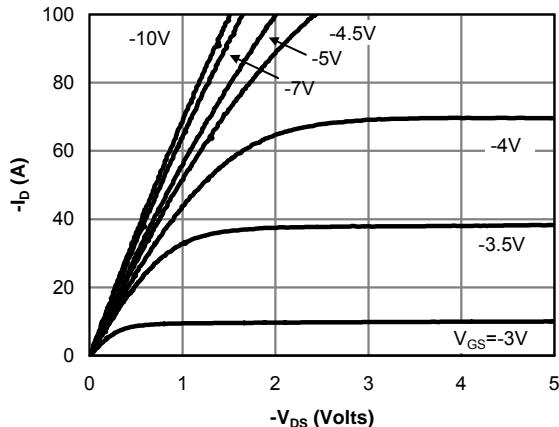
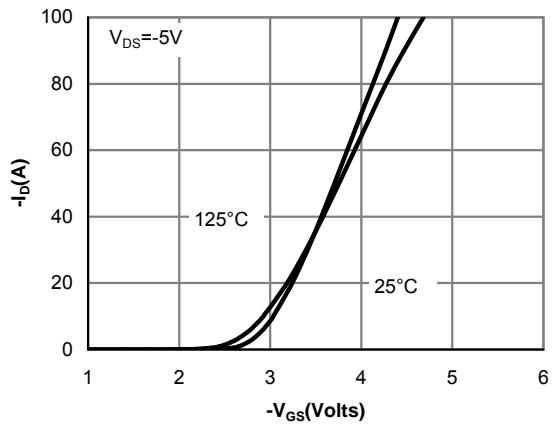
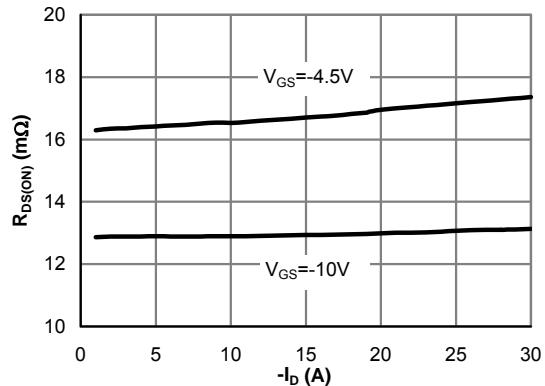
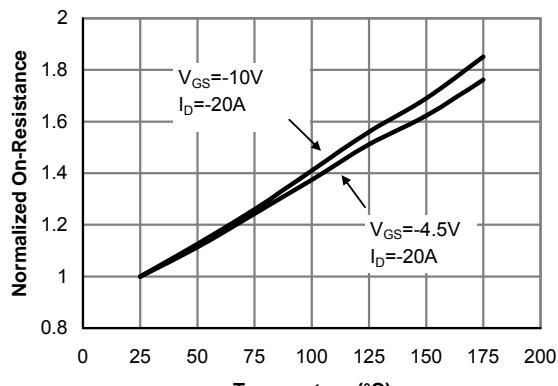
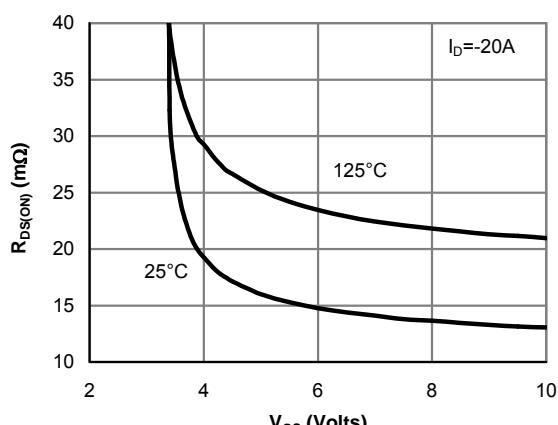
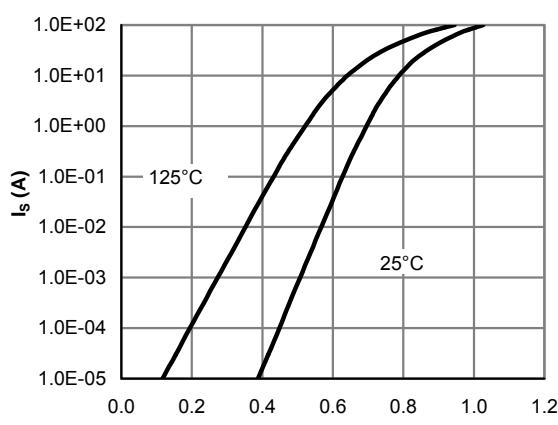
E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

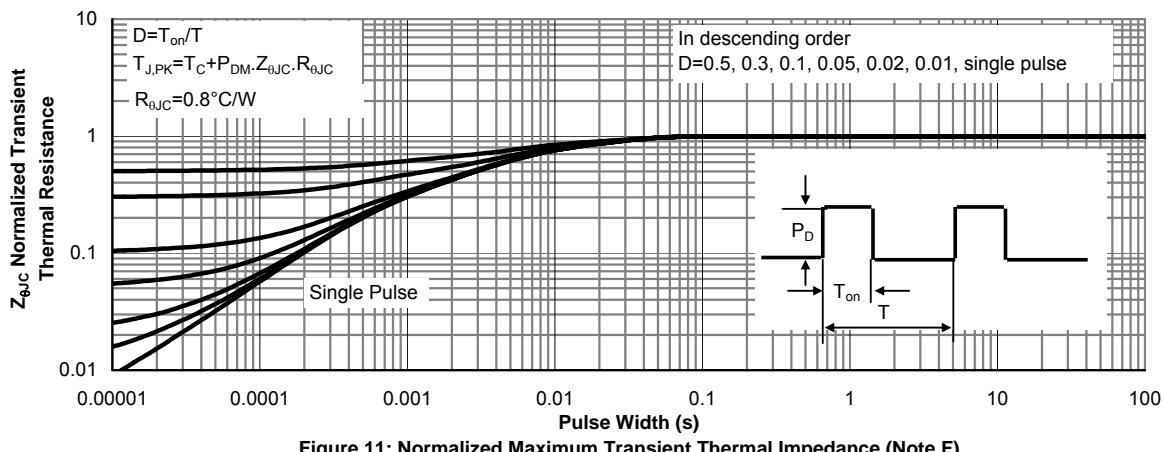
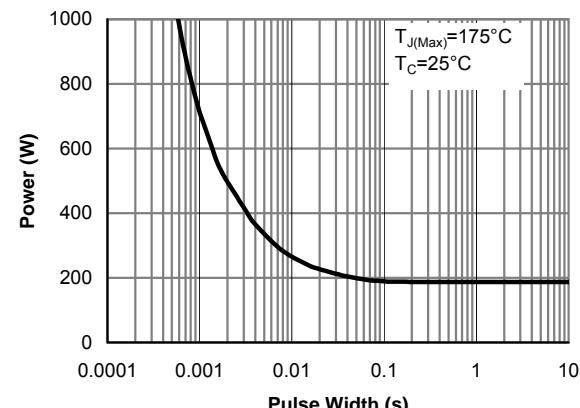
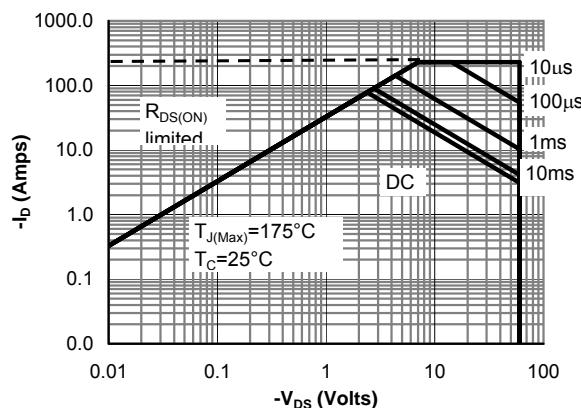
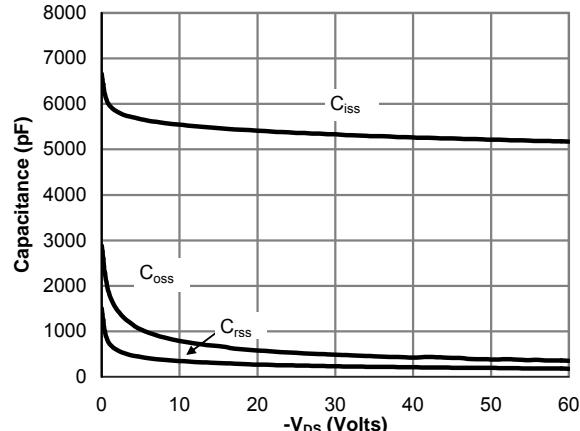
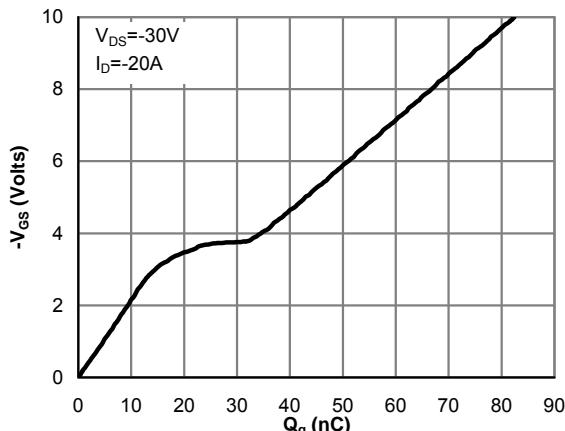
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

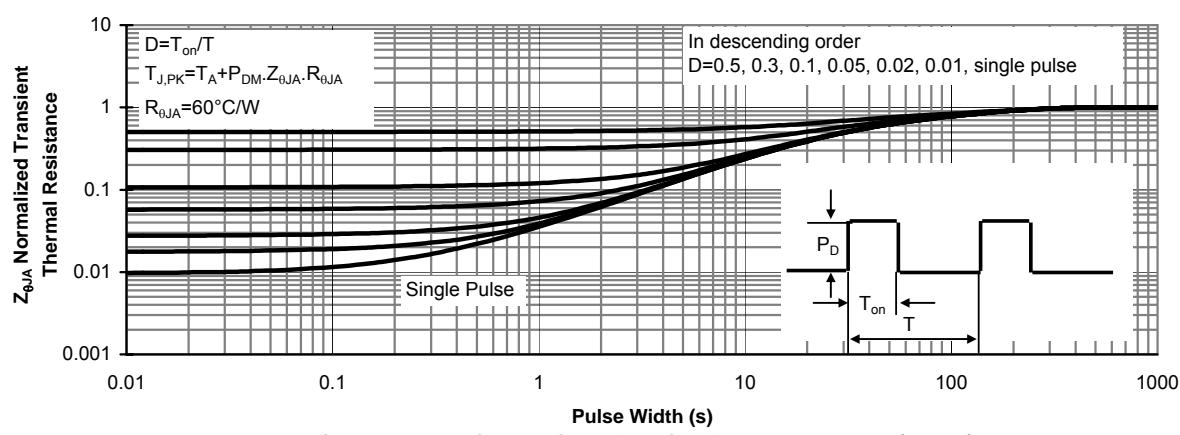
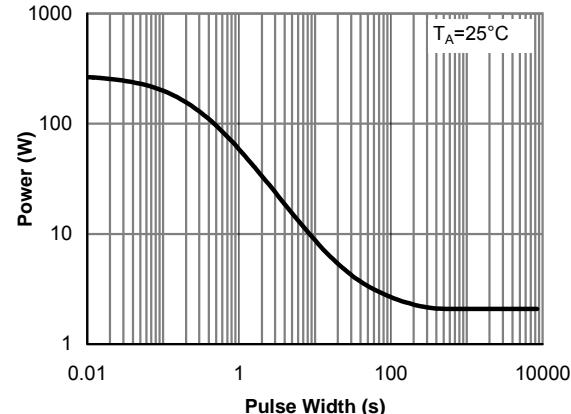
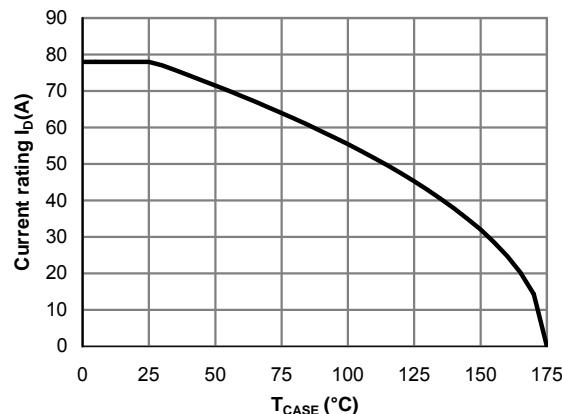
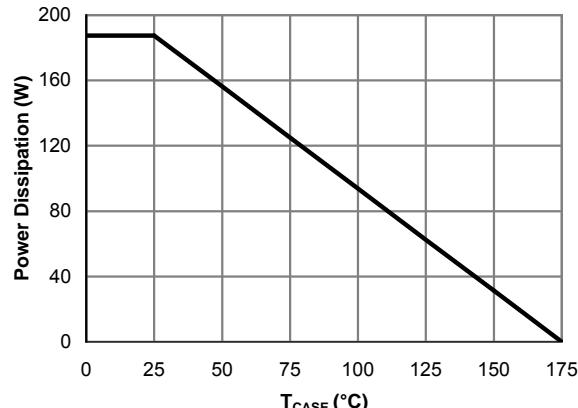
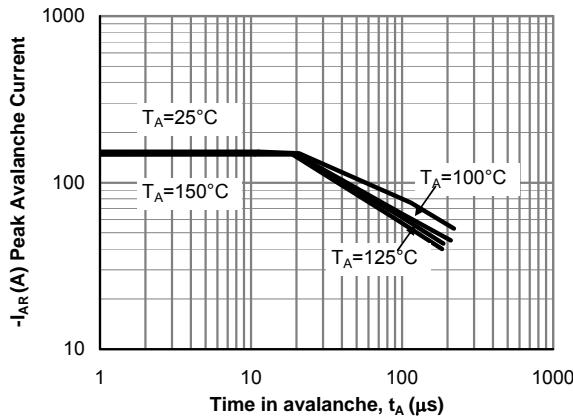
G. The maximum current limited by package.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

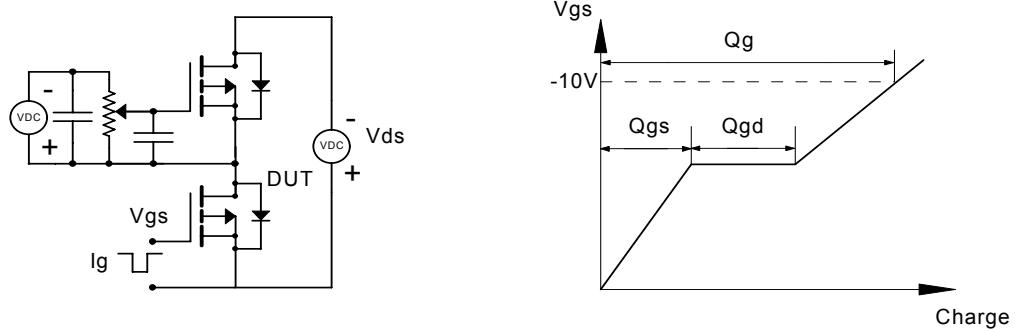
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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

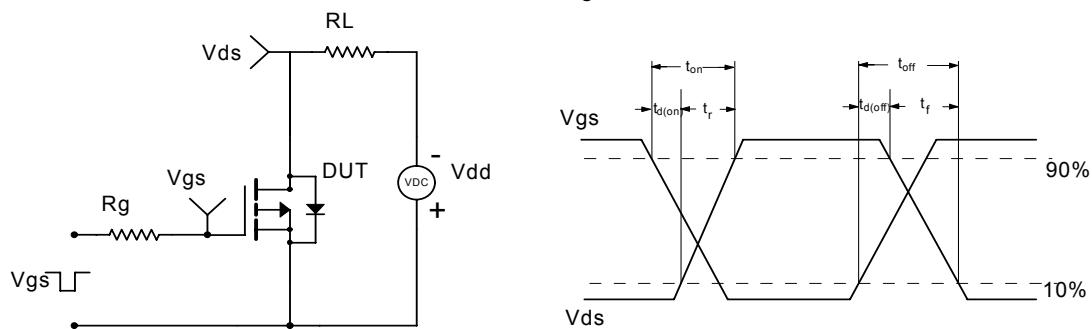
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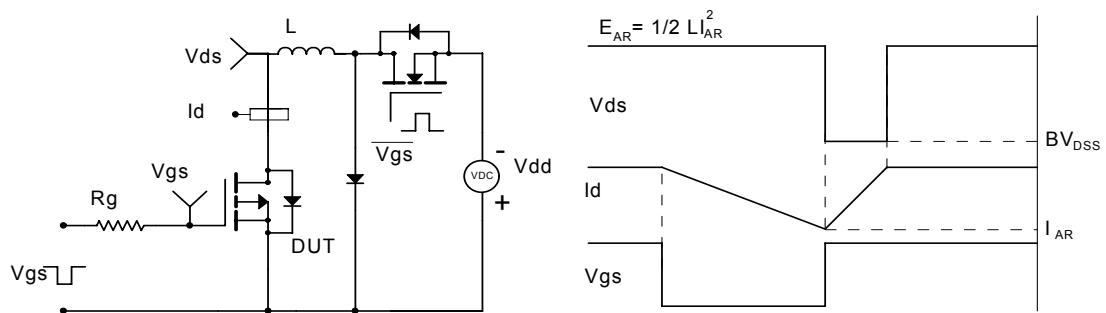
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

